

In the Claims:

1-19 (canceled)

20. (currently amended) A semiconductor device, comprising:

a package substrate having a top layer, the top layer having a group of conductive vias formed therethrough;

a layer of conductive material disposed ~~formed~~ on the top layer of the package substrate, said conductive material including contact pads and a plate layer spaced from the contact pads and having a thickness substantially equal to the thickness of the contact pads;

a group of channels disposed ~~formed~~ in the conductive material layer about at least some of the vias to define said ~~a group of~~ contact pads on the vias; ~~and~~

a semiconductor device ~~chip~~ electrically coupled to the package substrate through the contact pads; and

an electrically insulating underfill layer disposed over said plate layer and surrounding said conductive pads and filling the region between said semiconductor device and said package substrate.

21. (previously presented) The semiconductor device of claim 20, wherein the conductive layer comprises a metal selected from a group consisting of copper, aluminum, nickel, gold, and silver.

22. (previously presented) The semiconductor device of claim 20, wherein the conductive vias comprise a metal selected from a group consisting of copper, aluminum, nickel, gold, and silver.

23. (currently amended) The semiconductor device of claim 20, further comprising an oxide layer disposed ~~formed~~ over the conductive layer, ~~wherein~~ with portions of the oxide layer ~~have been~~ removed on at least some of the contact pads.

24. (currently amended) The semiconductor device of claim 23, further comprising solder balls soldered on at least some of the contact pads, ~~wherein the chip is~~ the semiconductor device electrically coupled to the contact pads on the package substrate via the solder balls.

25. (currently amended) The semiconductor device of claim 20, further comprising solder balls soldered on at least some of the contact pads, ~~wherein the chip is~~ electrically coupled to the contact pads on the package substrate ~~via the solder balls~~.

26 (new) The semiconductor device of claim 23 wherein the oxide layer is a finite amount up to about 1 micron.

27. (new) The semiconductor device of claim 20 wherein the thickness of the contact pad is substantially the same as the thickness of the remaining portion of the conductive material layer outside of the channel.

28. (new) The semiconductor device of claim 23 wherein the oxide layer is an oxide of the conductive material.

29. (new) A package for an integrated circuit device, comprising:

a package substrate;

an electrically conductive layer on a surface of said package substrate having conductive pads and a layer of substantially the same thickness as said conductive pads surrounding said conductive pads;

a semiconductor device having regions containing solder aligned with said contact pads and contacting said regions containing solder with said contact pads; and

an electrically insulating underfill layer disposed over said plate layer and surrounding said conductive pads and filling the region between said semiconductor device and said package substrate.

30. (new) The semiconductor device of claim 29 wherein said pads are formed of a material different from said layer of substantially the same thickness as said conductive layer.